



# BTA425X-800B

## 3Q Hi-Com Triac

17 July 2014

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series B" triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High immunity to false turn-on by  $dV/dt$
- High minimum IGT for guaranteed immunity to gate noise
- High voltage capability
- Isolated mounting base package
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high commutation capability with maximum false trigger immunity

## 3. Applications

- Electronic thermostats
- Heating control
- High power motor control
- High power switching

## 4. Quick reference data

Table 1. Quick reference data

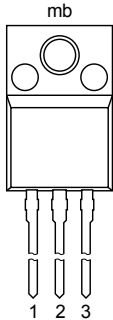
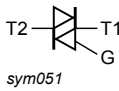
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	250	A
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 38\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	25	A
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7	-	-	50	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	2000	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 25\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	15	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220F (SOT186A)</p>	
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA425X-800B	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

## 7. Marking

Table 4. Marking codes

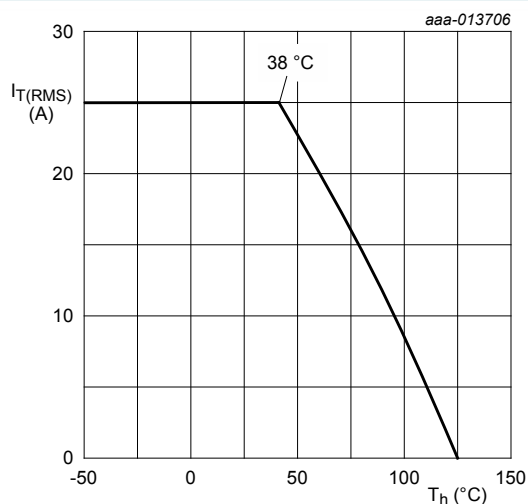
Type number	Marking code
BTA425X-800B	BTA425X-800B

## 8. Limiting values

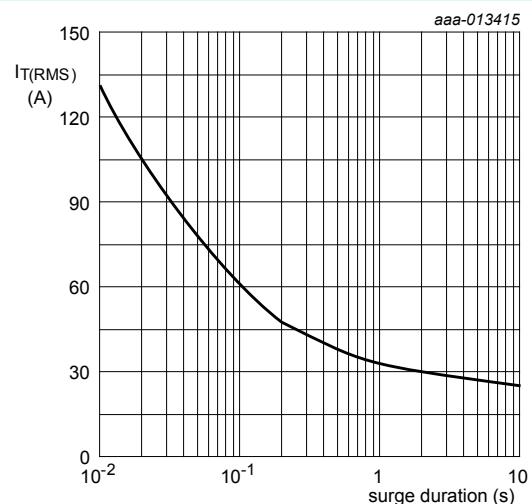
**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_h \leq 38\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	25	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	250	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$	-	275	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	312.5	$\text{A}^2\text{s}$
$di_{\text{T}}/dt$	rate of rise of on-state current	$I_{\text{T}} = 30\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current		-	2	A
$P_{\text{GM}}$	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
$T_{\text{stg}}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_{\text{j}}$	junction temperature		-	125	$^{\circ}\text{C}$



**Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_h = 38\text{ }^{\circ}\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

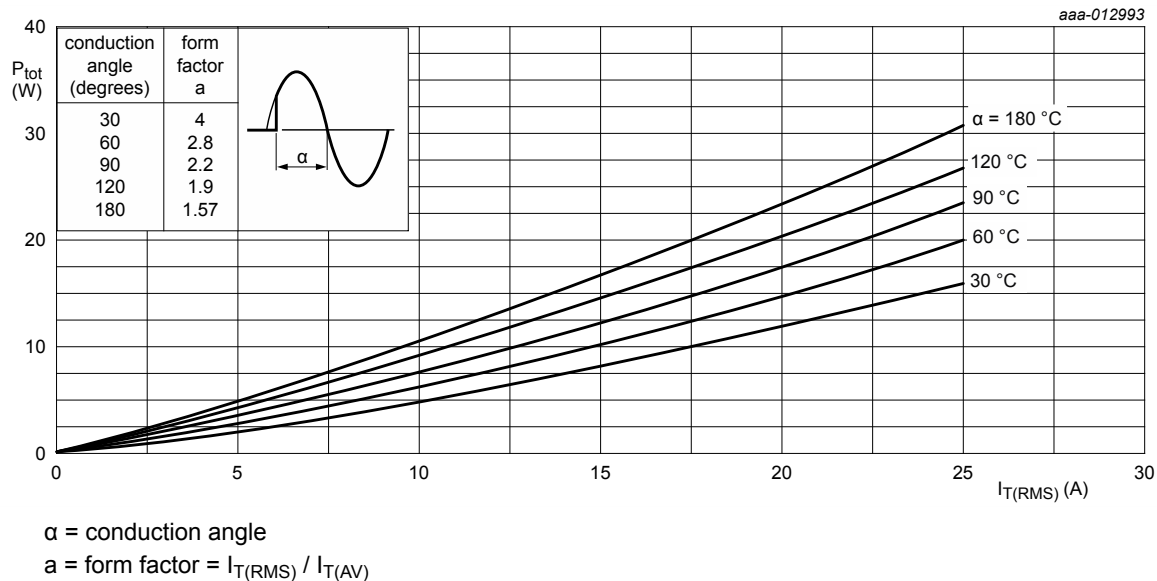


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

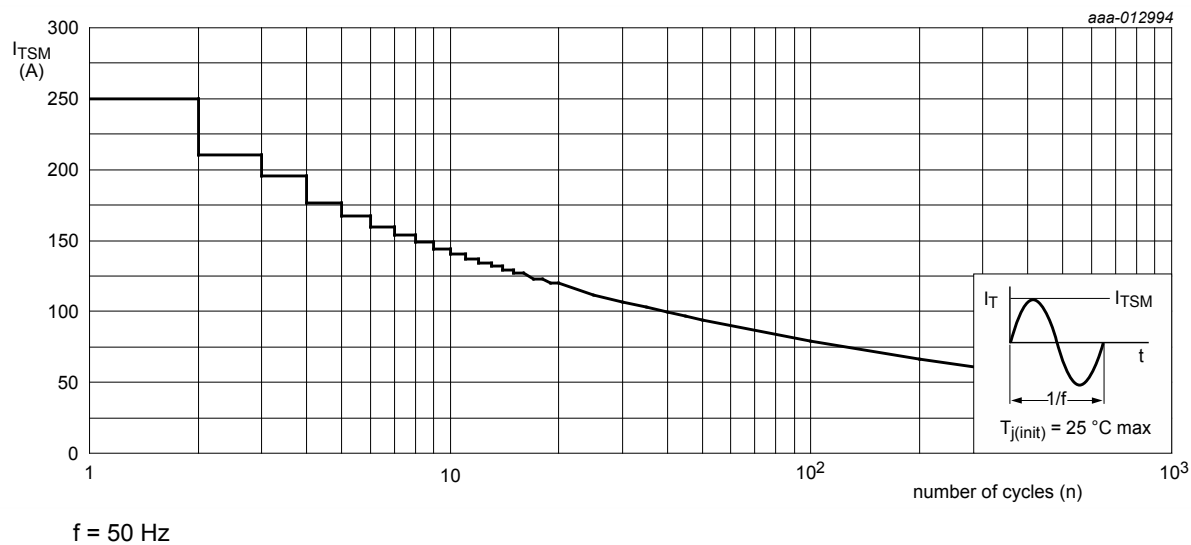
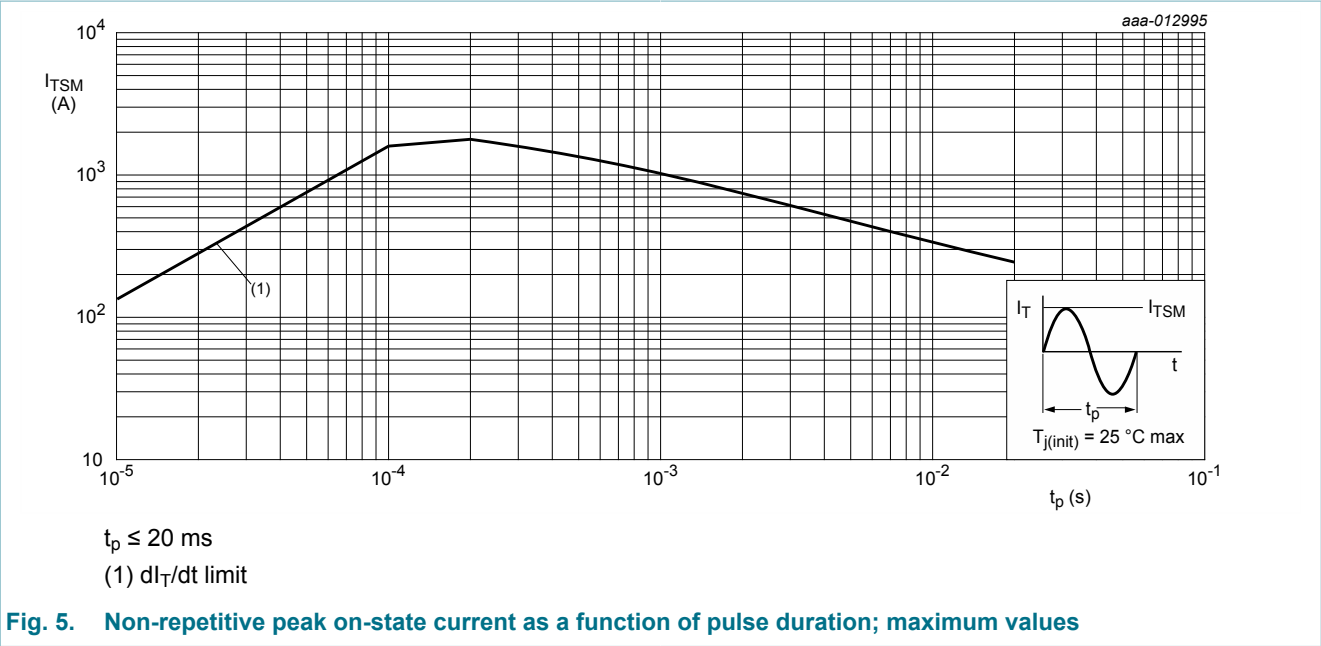


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle ; with heatsink compound; <a href="#">Fig. 6</a>	-	-	2.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

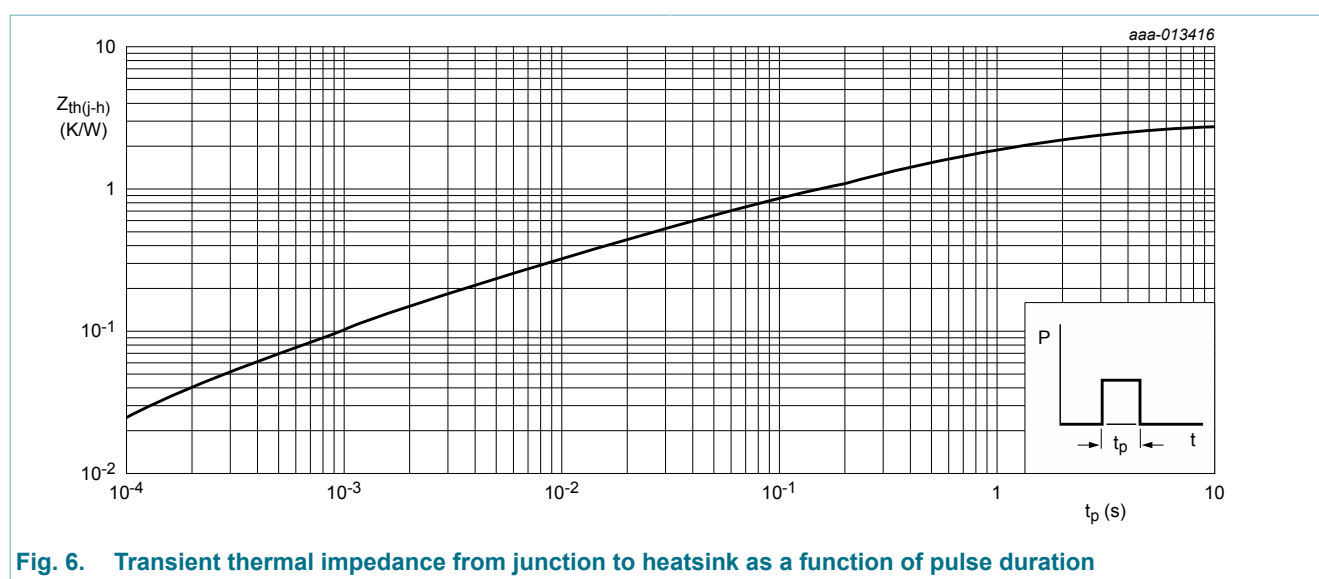


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

## 10. Isolation characteristics

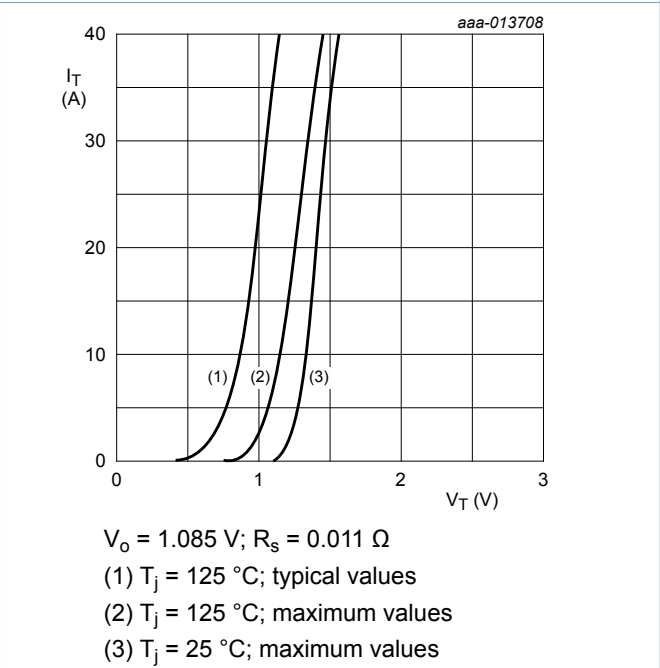
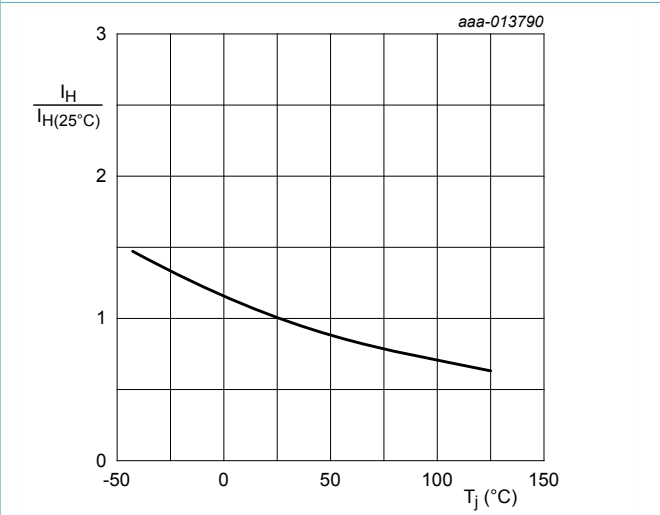
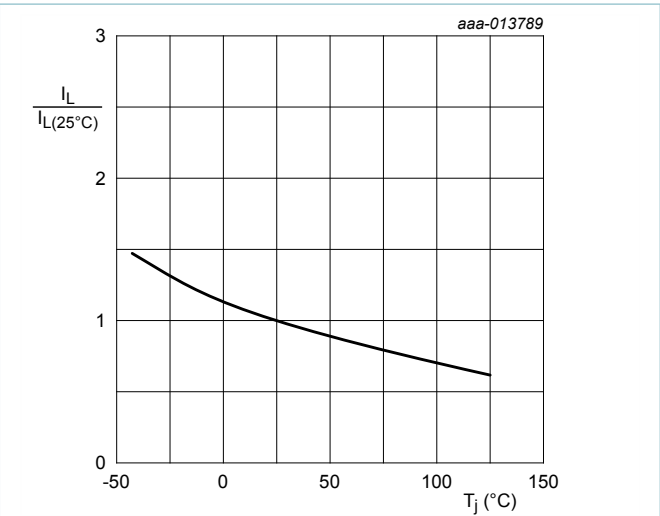
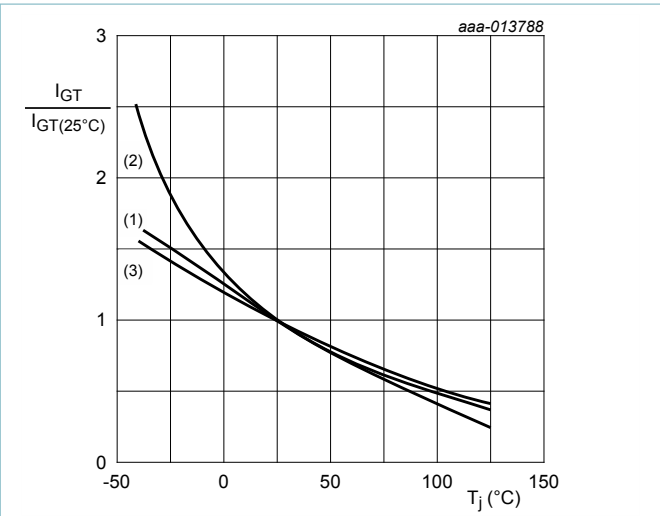
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
$C_{isol}$	isolation capacitance	from main terminal 2 to external heatsink; $f = 1\text{ MHz}$ ; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

## 11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	80	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	100	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	80	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	75	mA
$V_T$	on-state voltage	$I_T = 35\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	0.9	1.3	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	0.4	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	2000	-	-	V/ $\mu\text{s}$
$di_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 25\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	15	-	-	A/ms





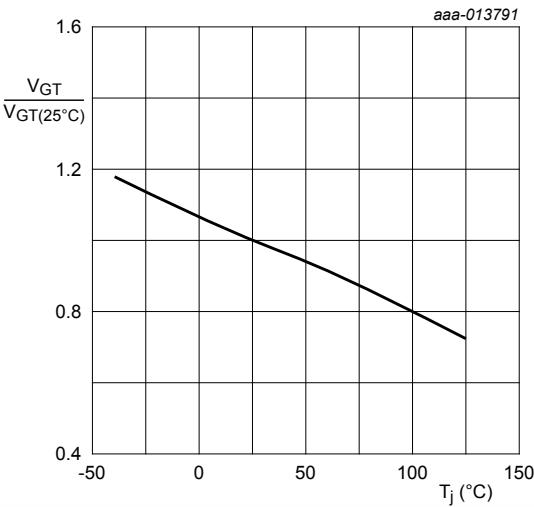


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

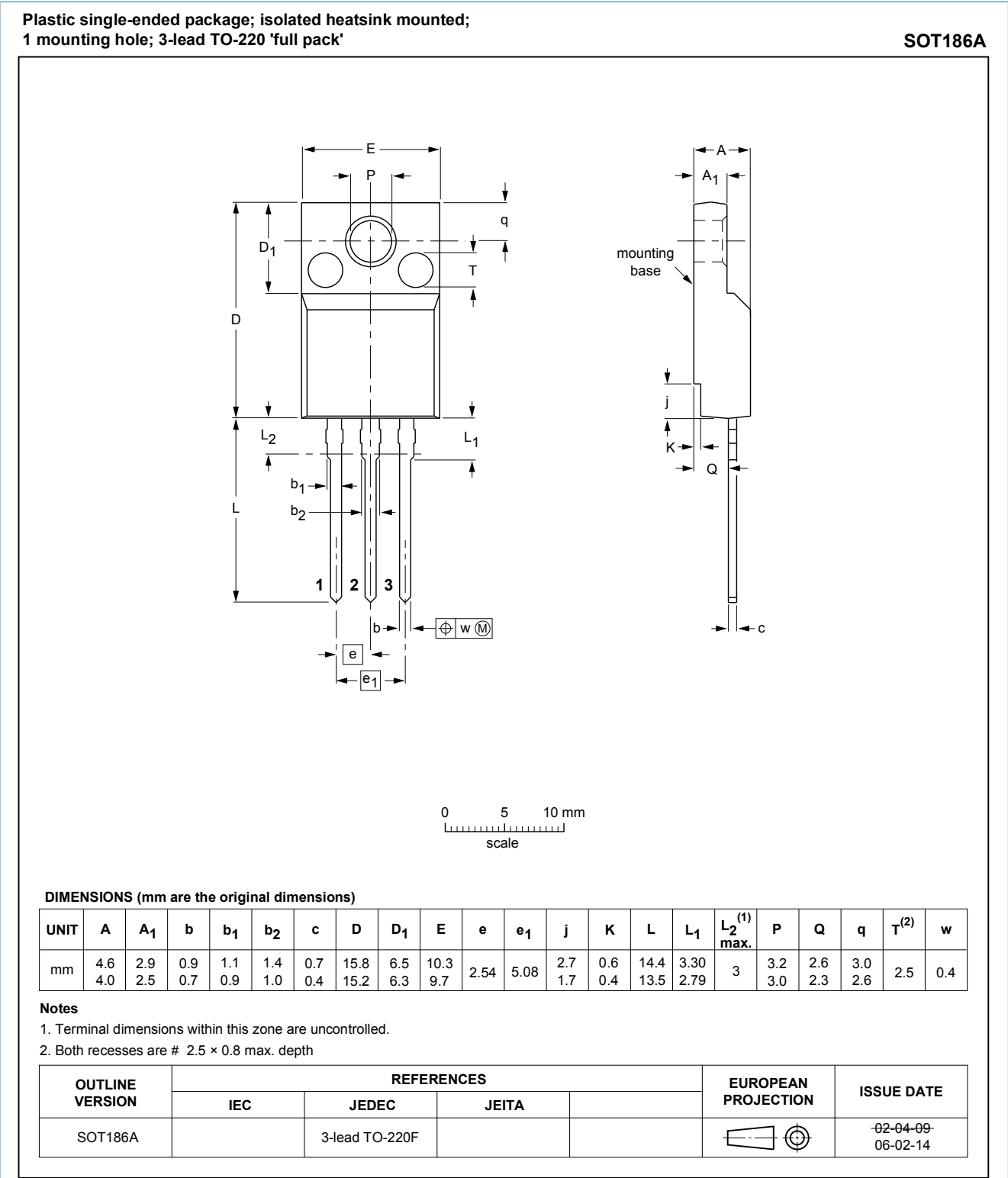


Fig. 12. Package outline TO-220F (SOT186A)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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